

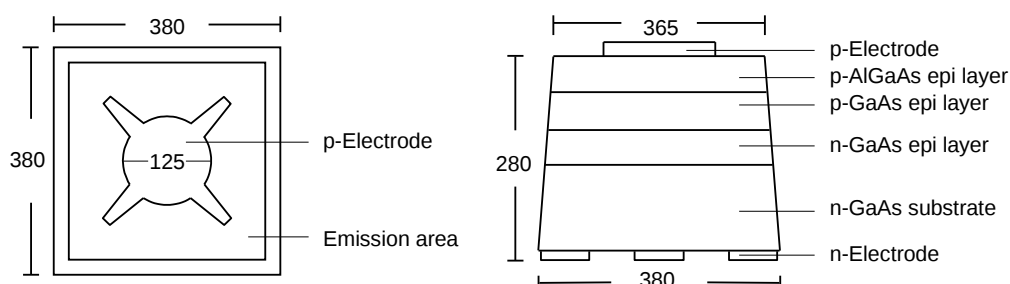
■ Features :

- AlGaAs/GaAs Wafer
- Good Spectral Matched to Si Detector
- High Power
- Low Forward Voltage

■ Typical Applications :

- Remote Controller
- Peripheral Device
- Photo Coupler
- Photo Interrupter

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	380 μm x 380 μm
	Thickness	280 μm
	Emission area	365 μm
	Bonding pad	125 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.19	1.35	V
		$I_F = 100 \text{ mA}$		1.32	1.65	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	940	-	nm
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	50	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	0.50	-	-	mW

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

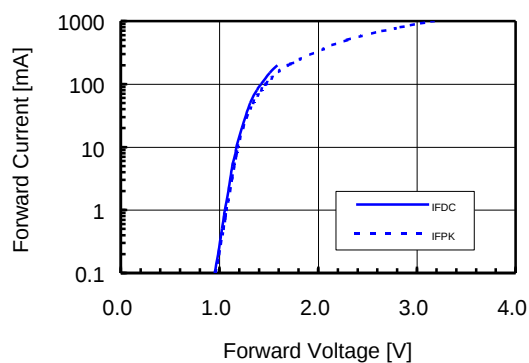


Fig 2. Relative Radiant Power vs. Wavelength

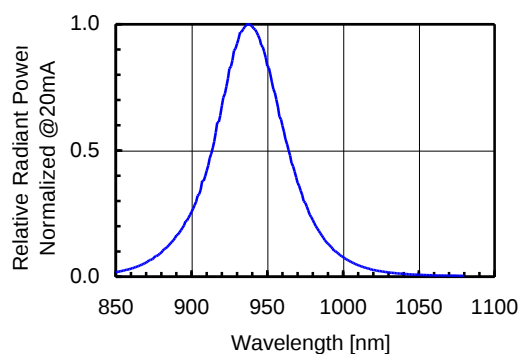
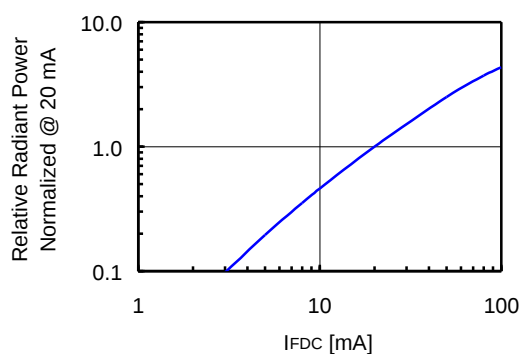
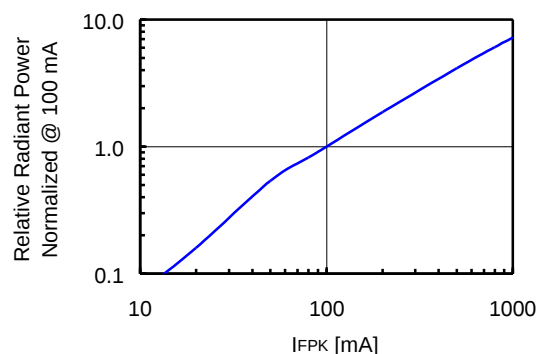
Fig 3. Relative Radiant Power
vs. Forward DC CurrentFig 4. Relative Radiant Power
vs. Forward Peak Current

Fig 5. Forward DC Voltage vs. Temperature

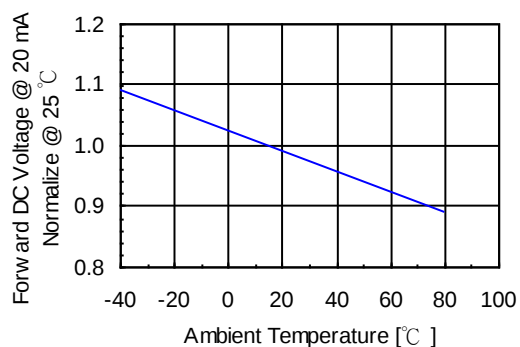


Fig 6. Relative Radiant Power vs. Temperature

